



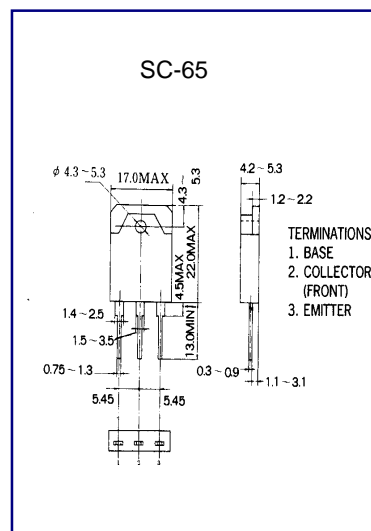
**2SD1063**

**NPN PLANAR SILICON TRANSISTOR**

- PSW / D / DDC
- COMPLEMENTARY TO 2SB827

**ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base voltage	V <sub>EBO</sub>	6	V
Collector Current (DC)	I <sub>C</sub>	7	A
Collector Dissipation	P <sub>C</sub>	60	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =5 mA I <sub>E</sub> =0	60			V
Collector Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =10 mA R <sub>BE</sub> =∞	50			V
Emitter Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =5mA I <sub>C</sub> =0	6			V
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =60V I <sub>E</sub> =0			0.1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V I <sub>C</sub> =0			0.1	mA
*DC Current Gain	H <sub>fe</sub>	V <sub>CE</sub> =2V I <sub>C</sub> =1A	70		280	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =4A I <sub>B</sub> =0.4A			0.4	V